

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. – 8. (Canceled)
9. (Previously Presented) A semiconductor device comprising:  
an element isolation region in a semiconductor substrate and an active area in the semiconductor substrate, the element isolation region isolating the active area in the semiconductor substrate, and the active area overlapping a top surface of the isolation region;  
an interlayer insulation film on the element isolation region and the active area and having an opening to which the element isolation region, the active area and a boundary therebetween are exposed;  
a glue layer in the opening; and  
a conductor on the glue layer.
10. (Previously Presented) The device according to claim 9, wherein the conductor is a metal layer.
11. (Previously Presented) The device according to claim 10, wherein the metal layer contains tungsten.
12. (Previously Presented) The device according to claim 9, wherein the glue layer contains an acid-resistant conductor.
13. (Previously Presented) The device according to claim 9, wherein the glue layer contains titanium.
14. (Previously Presented) The device according to claim 9, wherein the glue layer contains titanium nitride.

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15. (Previously Presented) The device according to claim 9, wherein the glue layer contains a layered film of titanium and titanium nitride.

16. (Previously Presented) The device according to claim 9, further comprising a reaction layer of a metal layer on a surface of the active area.

17. (Previously Presented) The device according to claim 16, wherein the reaction layer is a silicide layer.

18. (Previously Presented) The device according to claim 17, wherein the silicide layer contains titanium and silicon.

19. (Currently Amended) A semiconductor device comprising:  
an element isolation region in a semiconductor substrate, the element isolation region isolating an active area in the semiconductor substrate;  
a ~~semiconductor~~ silicide layer on a top surface of the active area, the ~~semiconductor~~ silicide layer overlapping the element isolation region;  
an interlayer insulation film on the element isolation region and the ~~semiconductor~~ silicide layer and having an opening to which the element isolation region, the ~~semiconductor~~ silicide layer and a boundary therebetween are exposed;  
a glue layer in the opening; and  
a conductor on the glue layer.

20. (Previously Presented) The device according to claim 19, wherein the conductor is a metal layer.

21. (Previously Presented) The device according to claim 20, wherein the metal layer contains tungsten.

22. (Previously Presented) The device according to claim 19, wherein the glue layer contains an acid-resistant conductor.

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23. (Previously Presented) The device according to claim 19, wherein the glue layer contains titanium.

24. (Previously Presented) The device according to claim 19, wherein the glue layer contains titanium nitride.

25. (Previously Presented) The device according to claim 19, wherein the glue layer contains a layered film of titanium and titanium nitride.

26. – 27. (Canceled)

28. (Currently Amended) The device according to claim ~~[[27]]~~ 19, wherein the silicide layer contains titanium and silicon.

29. (Currently Amended) A semiconductor device comprising:  
an element isolation region in a semiconductor substrate, the element isolation region isolating an active area in the semiconductor substrate and having a hollow in the element isolation region to which a side surface of the active area faces;  
a ~~semiconductor~~ silicide layer on a top surface of the active area in the hollow;  
an interlayer insulation film on the element isolation region and the ~~semiconductor~~ silicide layer and having an opening to which the element isolation region, the ~~semiconductor~~ silicide layer and a boundary therebetween are exposed;  
a glue layer in the opening; and  
a conductor on the glue layer.

30. (Previously Presented) The device according to claim 29, wherein the conductor is a metal layer.

31. (Previously Presented) The device according to claim 30, wherein the metal layer contains tungsten.

32. (Previously Presented) The device according to claim 29, wherein the glue layer contains an acid-resistant conductor

33. (Previously Presented) The device according to claim 29, wherein the glue layer contains titanium.

34. (Previously Presented) The device according to claim 29, wherein the glue layer contains titanium nitride.

35. (Previously Presented) The device according to claim 29, wherein the glue layer contains a layered film of titanium and titanium nitride.

36. – 37. (Canceled)

38 (Currently Amended) The device according to claim ~~[[37]]~~ 29, wherein the silicide layer contains titanium and silicon.